

# SCT2080KE

# N-channel SiC power MOSFET

$V_{\mathrm{DSS}}$	1200V
$R_{DS(on)}(Typ.)$	$80$ m $\Omega$
I <sub>D</sub>	40A
$P_D$	262W

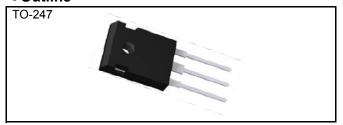
### Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

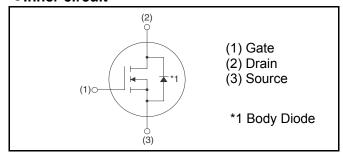
## Application

- Solar inverters
- DC/DC converters
- Induction heating
- Motor drives

### Outline



## •Inner circuit



## Packaging specifications

	Packing	Tube
	Reel size (mm)	-
Typo	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	30
	Packing code	С
	Marking	SCT2080KE

## ● Absolute maximum ratings (T<sub>a</sub> = 25°C)

Parameter		Symbol	Value	Unit
Drain - Source voltage		$V_{ extsf{DSS}}$	1200	V
Continuous drain current	T <sub>c</sub> = 25°C	I <sub>D</sub> *1	40	А
Continuous drain current	T <sub>c</sub> = 100°C	I <sub>D</sub> <sup>*1</sup>	28	Α
Pulsed drain current		I <sub>D,pulse</sub> *2	80	А
Gate - Source voltage (DC)		$V_{GSS}$	−6 to 22	V
Gate - Source surge voltage (T <sub>surge</sub> < 300nsec)		$V_{GSS\text{-surge}}^{*3}$	−10 to 26	V
Power dissipation (T <sub>c</sub> = 25°C)		$P_{D}$	262	W
Junction temperature		T <sub>j</sub>	175	°C
Range of storage temperature		T <sub>stg</sub>	-55 to +175	°C

## ●Thermal resistance

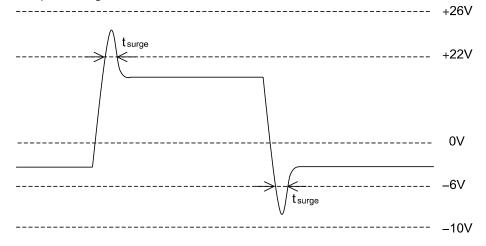
Parameter	Symbol	Values			Unit
- Faranietei	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	$R_{thJC}$	-	0.44	0.57	°C/W
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	50	°C/W
Soldering temperature, wavesoldering for 10s	T <sub>sold</sub>	-	-	265	°C

# ●Electrical characteristics (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
r ai ai ii e lei	Syllibol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	1200	ı	ı	V
		$V_{DS} = 1200V, V_{GS} = 0V$				
Zero gate voltage drain current	I <sub>DSS</sub>	T <sub>j</sub> = 25°C	-	1	10	μΑ
		T <sub>j</sub> = 150°C	-	2	-	
Gate - Source leakage current	$I_{\mathrm{GSS}^+}$	$V_{GS} = +22V, V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	I <sub>GSS-</sub>	$V_{GS} = -6V, V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	V <sub>GS (th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 4.4 \text{mA}$	1.6	2.8	4.0	V

<sup>\*1</sup> Limited only by maximum temperature allowed.

<sup>\*3</sup> Example of acceptable Vgs waveform



\*4 Pulsed

<sup>\*2</sup> PW  $\leq$  10 $\mu$ s, Duty cycle  $\leq$  1%

# ●Electrical characteristics (T<sub>a</sub> = 25°C)

Parameter	Cymbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
		$V_{GS} = 18V, I_D = 10A$				
Static drain - source on - state resistance	R <sub>DS(on)</sub> *4	T <sub>j</sub> = 25°C	-	80	117	mΩ
		T <sub>j</sub> = 125°C	-	125	-	
Gate input resistance	$R_G$	f = 1MHz, open drain	-	6.3	-	Ω
Transconductance	g <sub>fs</sub> *4	$V_{DS} = 10V, I_{D} = 10A$	-	3.7	-	S
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	2080	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 800V	-	77	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	16	-	
Effective output capacitance, energy related	C <sub>o(er)</sub>	$V_{GS} = 0V$ $V_{DS} = 0V$ to 500V	-	116	-	pF
Turn - on delay time	t <sub>d(on)</sub> *4	V <sub>DD</sub> = 400V, V <sub>GS</sub> = 18V	-	35	-	
Rise time	t <sub>r</sub> *4	I <sub>D</sub> = 10A	-	36	-	20
Turn - off delay time	t <sub>d(off)</sub> *4	$R_L = 40\Omega$	-	76	-	ns
Fall time	t <sub>f</sub> *4	$R_G = 0\Omega$	-	22	-	
Turn - on switching loss	E <sub>on</sub> *4	$V_{DD} = 600V, I_{D} = 10A$ $V_{GS} = 18V/0V$	1	174	1	1
Turn - off switching loss	E <sub>off</sub> *4	R <sub>G</sub> = 0Ω, L=500μH *E <sub>on</sub> includes diode reverse recovery	-	51	-	μJ

# ●Gate Charge characteristics (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
r ai ai ii e lei	Symbol	Conditions	Min.	Тур.	Max.	Oill
Total gate charge	Qg *4	V <sub>DD</sub> = 400V	ı	106	ı	
Gate - Source charge	Q <sub>gs</sub> *4	I <sub>D</sub> = 10A	-	27	-	nC
Gate - Drain charge	Q <sub>gd</sub> *4	V <sub>GS</sub> = 18V	-	31	-	
Gate plateau voltage	V <sub>(plateau)</sub>	$V_{DD} = 400V, I_D = 10A$	-	9.7	-	V

# ●Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
raiainetei	Syllibol	Conditions	Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	I <sub>S</sub> *1	-T <sub>c</sub> = 25°C	ı	-	40	А
Inverse diode direct current, pulsed	I <sub>SM</sub> *2		-	-	80	Α
Forward voltage	V <sub>SD</sub> *4	V <sub>GS</sub> = 0V, I <sub>S</sub> = 10A	-	4.6	-	V
Reverse recovery time	t <sub>rr</sub> *4		ı	31	ı	ns
Reverse recovery charge	Q <sub>rr</sub> *4	I <sub>F</sub> = 10A, V <sub>R</sub> = 400V di/dt = 150A/μs	-	44	-	nC
Peak reverse recovery current	I <sub>rrm</sub> *4		-	2.3	-	Α

# ● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R <sub>th1</sub>	0.078	
R <sub>th2</sub>	0.197	K/W
R <sub>th3</sub>	0.162	

Symbol	Value	Unit
C <sub>th1</sub>	0.005	
C <sub>th2</sub>	0.018	Ws/K
C <sub>th3</sub>	0.249	

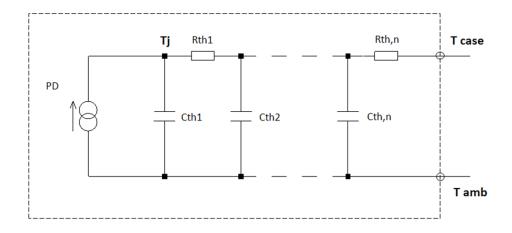


Fig.1 Power Dissipation Derating Curve

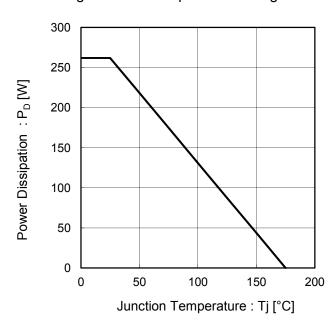


Fig.2 Maximum Safe Operating Area

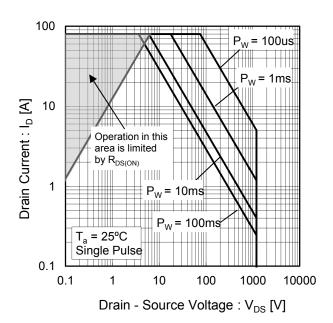


Fig.4 Typical Output Characteristics(I)

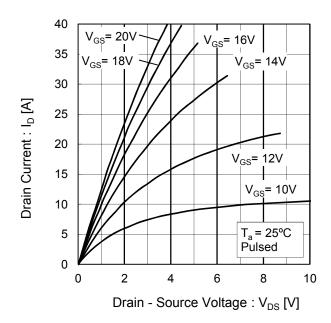


Fig.5 Typical Output Characteristics(II)

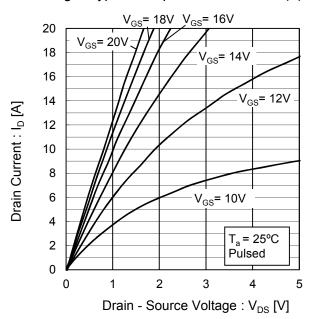


Fig.6 Typical Output Characteristics(I)

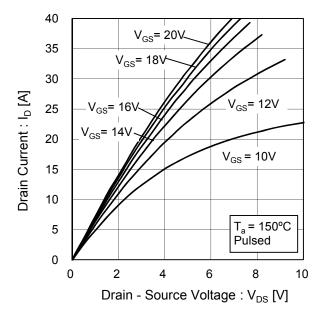


Fig.7 Typical Output Characteristics(II)

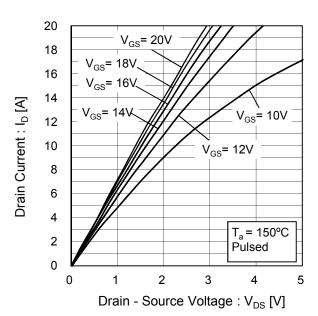


Fig.8 Typical Transfer Characteristics

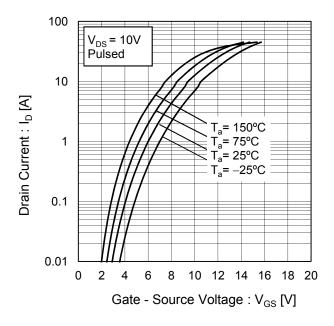


Fig.9 Typical Transfer Characteristics (II)

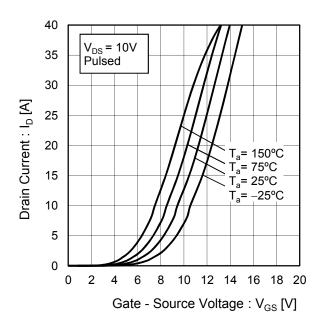


Fig.10 Gate Threshold Voltage vs. Junction Temperature

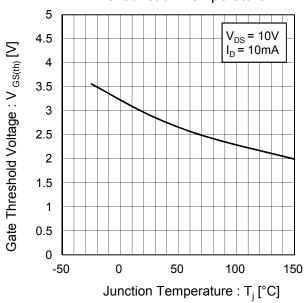


Fig.11 Transconductance vs. Drain Current

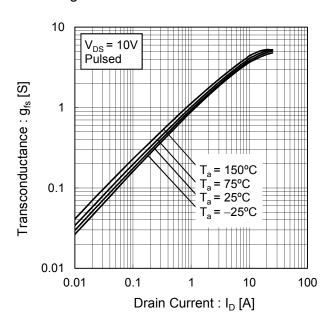


Fig.12 Static Drain - Source On - State Resistance vs. Gate - Source Voltage 8.0 Static Drain - Source On-State Resistance T<sub>a</sub> = 25°C Pulsed 0.6  $:R_{DS(on)}\left[ \Omega \right]$ 0.4  $I_{\rm D} = 20A$ 0.2  $I_D = 10A$ 0 6 8 10 12 14 16 18 20 22 Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

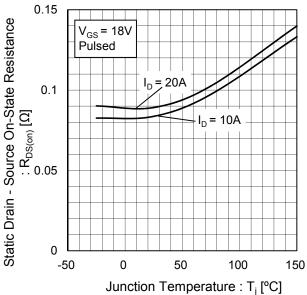
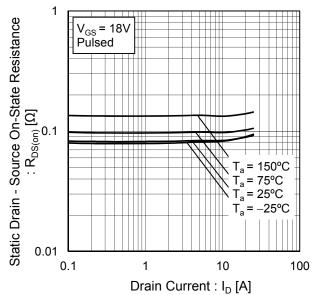
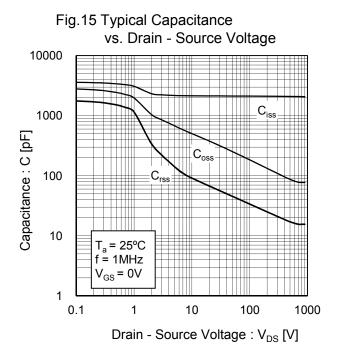


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current





40 T<sub>a</sub> = 25°C [n]] 30 : Coss Stored Energy 20 10 0

Fig.16 Coss Stored Energy

Fig.17 Switching Characteristics

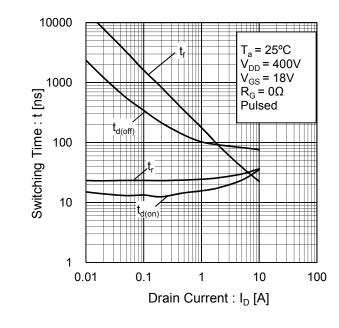


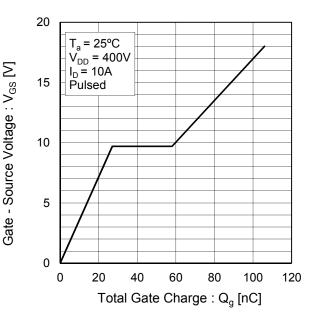
Fig.18 Dynamic Input Characteristics

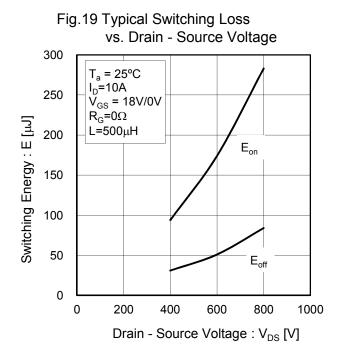
400

Drain - Source Voltage : V<sub>DS</sub> [V]

600

800





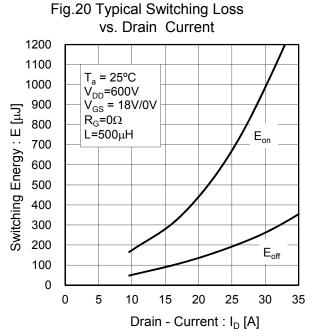
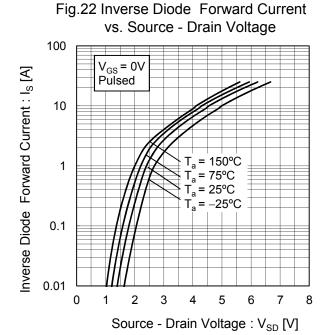
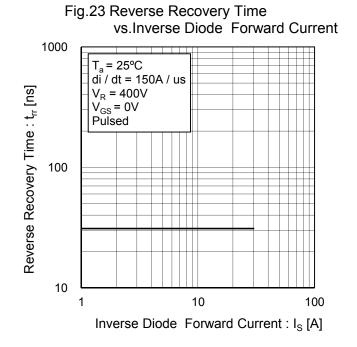


Fig.21 Typical Switching Loss vs. External Gate Resistance 500 T<sub>a</sub> = 25°C 450 V<sub>DD</sub>=600V 400  $I_D = 10A$  $V_{GS} = 18V/0V$ L=500µH Switching Energy : E [µJ] 350 300 250 200 150  $\mathsf{E}_{\mathsf{off}}$ 100 50 0 5 0 10 15 20 30 25 External Gate Resistance :  $R_G [\Omega]$ 

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### Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

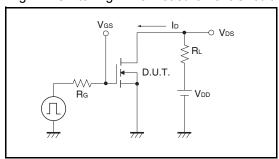


Fig.2-1 Gate Charge Measurement Circuit

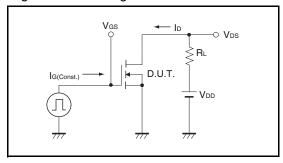


Fig.3-1 Switching Energy Measurement Circuit

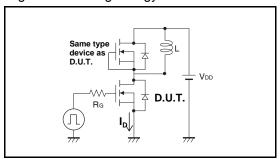


Fig.4-1 Reverse Recovery Time Measurement Circuit Fig.4-2 Reverse Recovery Waveform

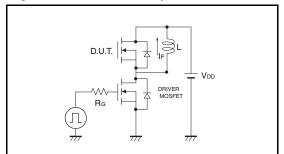


Fig.1-2 Switching Waveforms

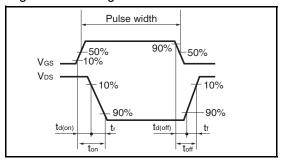


Fig.2-2 Gate Charge Waveform

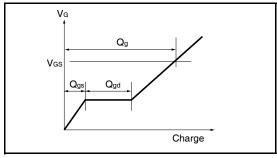
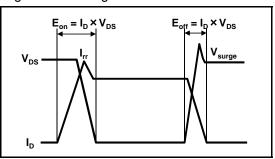
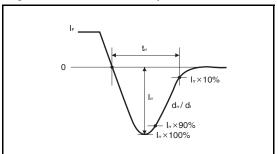


Fig.3-2 Switching Waveforms





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